

N-Channel Enhancement Mode Power MOSFET

Description

The HM250N03GA uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

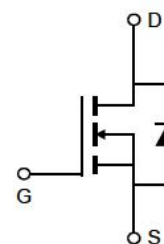
- $V_{DS} = 30V$, $I_D = 250A$
 $R_{DS(ON)} = 0.9m\Omega$ (Typ) @ $V_{GS}=10V$
 $R_{DS(ON)} = 1.8m\Omega$ (Typ) @ $V_{GS}=4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

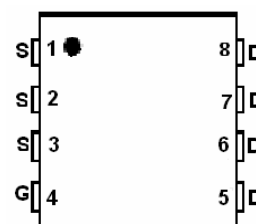
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



DFN5X6-8L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM250N03GA	HM250N03GA	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	250	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	175	A
Pulsed Drain Current	I_{DM}	750	A
Maximum Power Dissipation	P_D	235	W
Derating factor		1.57	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	2381	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.64	°C/W
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

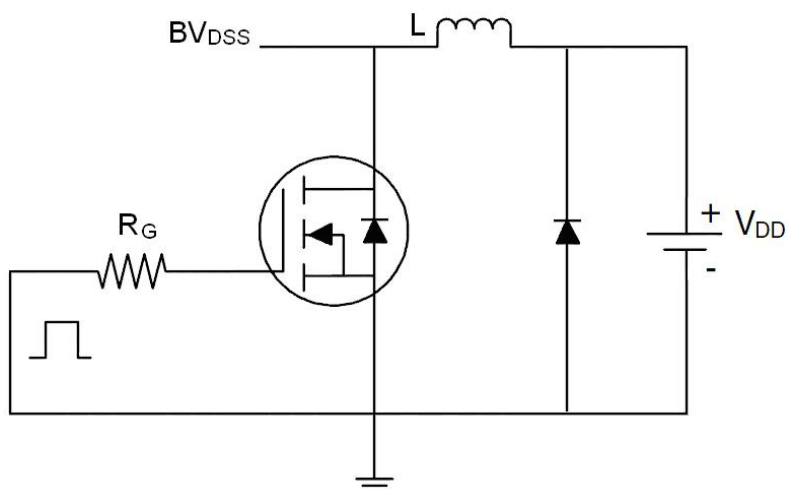
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	-	2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	0.9	1.4	mΩ
		V _{GS} =4.5V, I _D =20A	-	1.8	2.2	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =40A	-	90	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	10100	-	pF
Output Capacitance	C _{OSS}		-	1590	-	pF
Reverse Transfer Capacitance	C _{rss}		-	1060	-	pF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =15Ω, R _G =2.5Ω, V _{GS} =10V	-	30	-	nS
Turn-on Rise Time	t _r		-	140	-	nS
Turn-Off Delay Time	t _{d(off)}		-	70	-	nS
Turn-Off Fall Time	t _f		-	90	-	nS
Total Gate Charge	Q _g	I _D =20A, V _{DD} =15V, V _{GS} =10V	-	228	-	nC
Gate-Source Charge	Q _{gs}		-	40.5	-	nC
Gate-Drain Charge	Q _{gd}		-	61.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	250	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 40A di/dt = 100A/μs (Note3)	-	45	-	nS
Reverse Recovery Charge	Q _{rr}		-	160	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

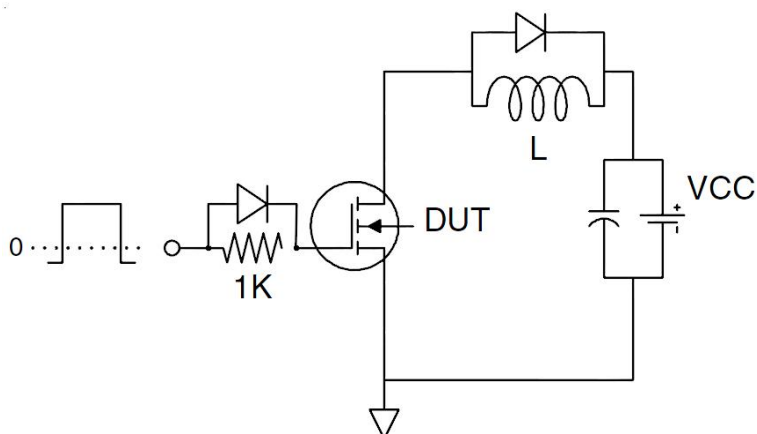
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, L=0.5mH, R_G=25\Omega$

Test circuit

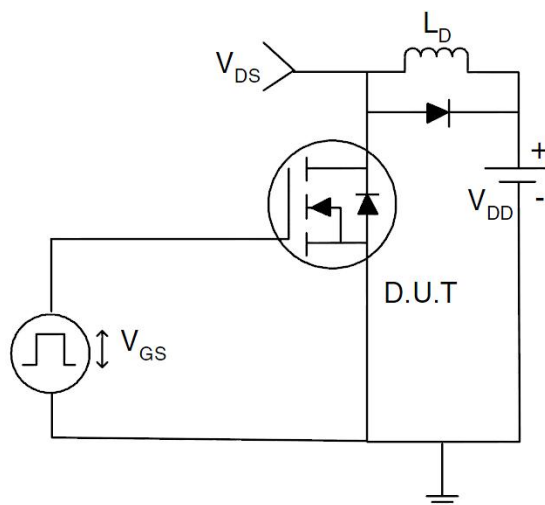
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

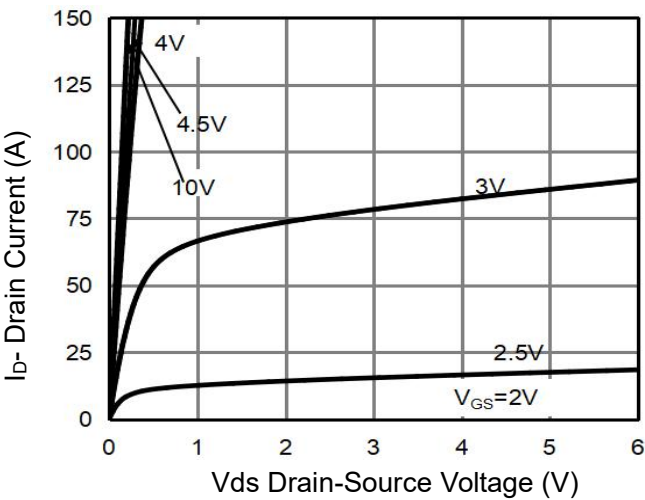


Figure 1 Output Characteristics

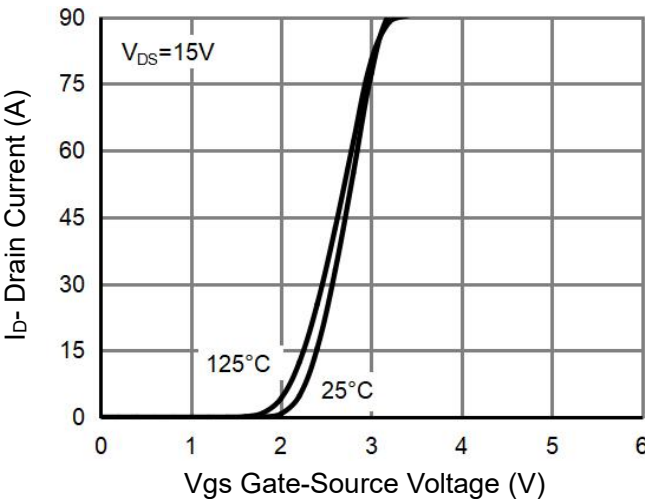


Figure 2 Transfer Characteristics

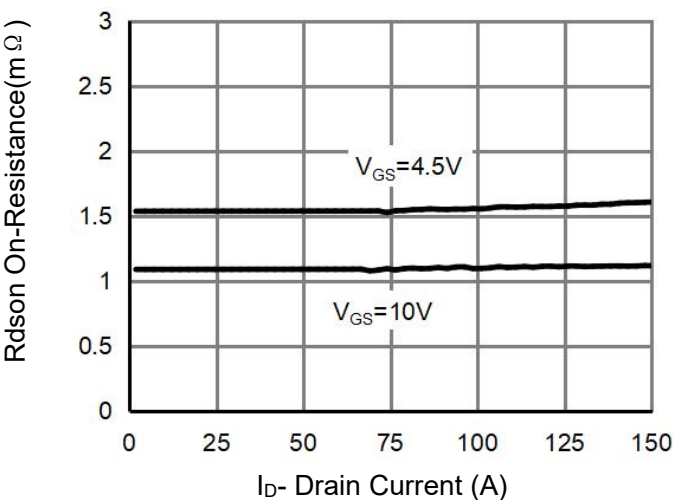


Figure 3 Rdson- Drain Current

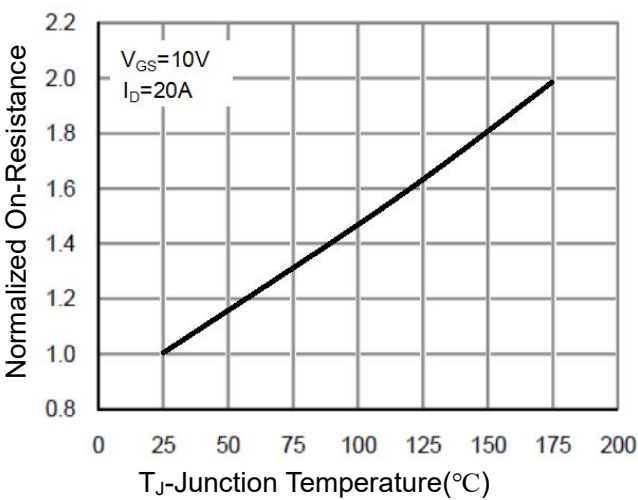


Figure 4 Rdson-Junction Temperature

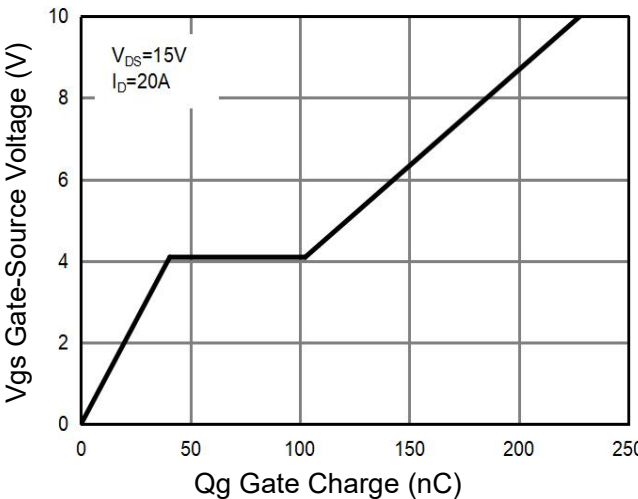


Figure 5 Gate Charge

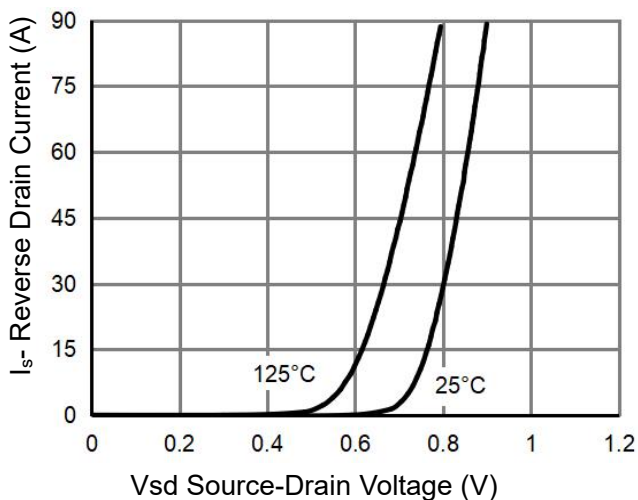


Figure 6 Source- Drain Diode Forward

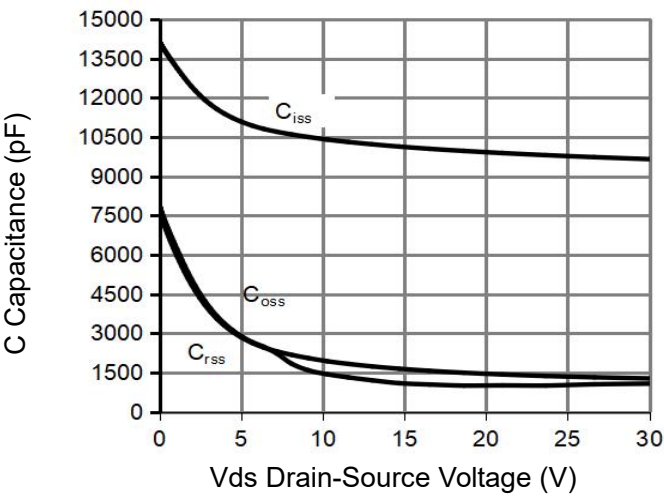


Figure 7 Capacitance vs Vds

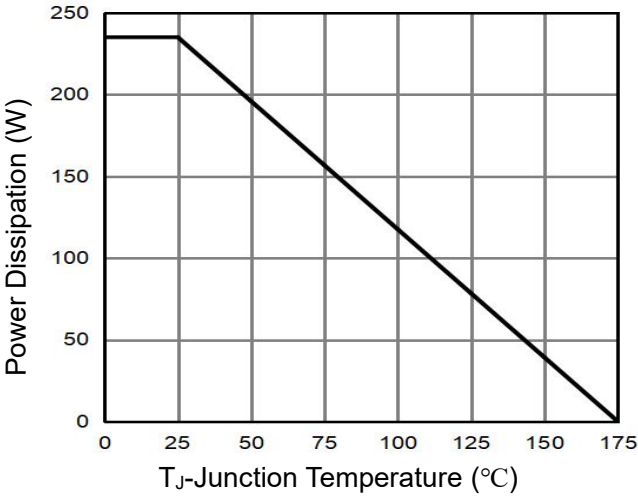


Figure 9 Power De-rating

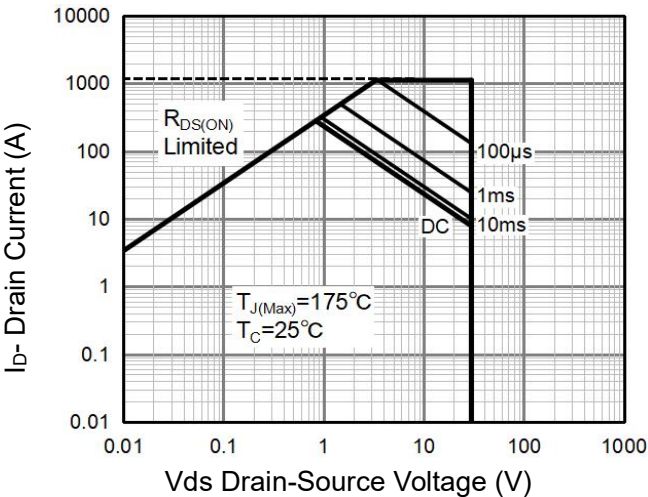


Figure 8 Safe Operation Area

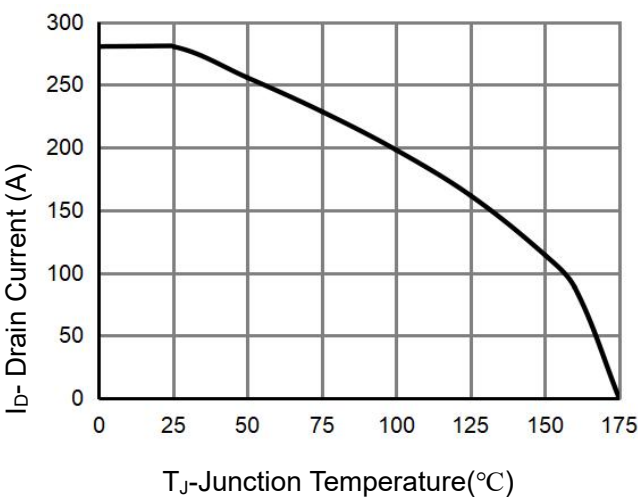


Figure 10 Current vs Junction Temperature

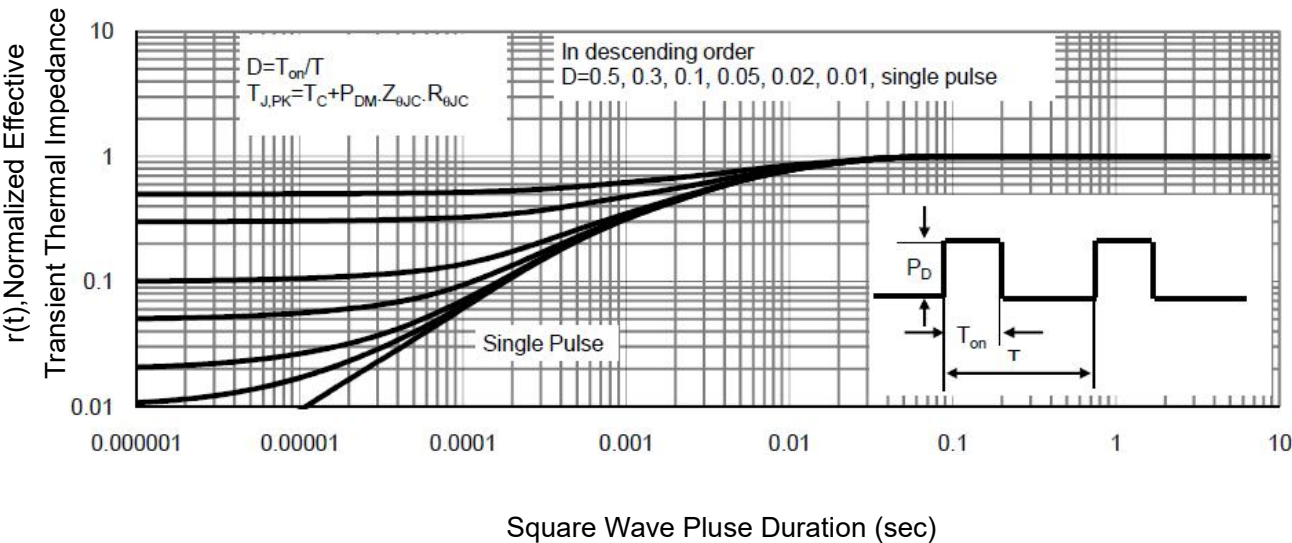
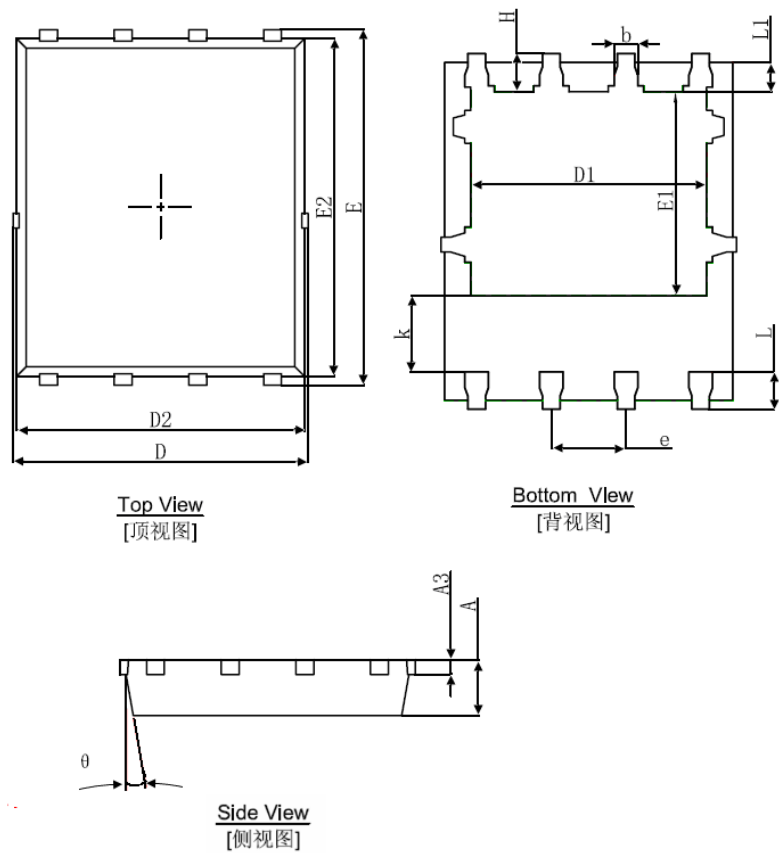


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	8°	12°	8°	12°